

New Mechanism of Magnetoresistance in Bulk Semiconductors: Boundary Condition Effects

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Abstract

We consider the electronic transport in bounded semiconductors in the presence of an external magnetic field. Taking into account appropriate boundary conditions for the current density at the contacts, a change in the magnetoresistance of bulk semiconductors is found as compared with the usual theory of galvanomagnetic effects in boundless media. New mechanism in magnetoresistance connected with the boundary conditions arises. In particular, even when the relaxation time is independent of the electron energy, magnetoresistance is not vanish.

Key words: A. semiconductors, D. electronic transport, D. galvanomagnetic effects

It is well known that magnetoresistance means the increasing in the electrical resistance of a metal or semiconductor when placed in a magnetic field. The effect of greatest interest is the transverse magnetoresistance, which is usually studied in the following geometrical arrangement: a long conducting channel is directed along the x -axis, and a uniform electric field E_x is established in the channel by means of an external power supply. A uniform magnetic field B is applied along the y -axis, thus normal to the axis of the channel. As a result of the geometry of the sample the carriers are deviated from the x direction and an electric field (Hall field) appears as a consequence of the accumulation of carriers on the surface of the sample in the z direction. The electrical current along the Hall field is usually considered zero in the standard theory of magnetoresistance after reach steady state conditions.

In the geometry described before, the effect of weak magnetic field $\omega_H \tau \ll 1$, where ω_H is the cyclotron frequency and τ the relaxation time, is to increase

the resistance by an additive term proportional to B^2 .

There are two important mechanisms in magnetoresistance in the conventional theory: one of them is connected with the dependence of the electric conductivity on the magnetic field (physical magnetoresistance), and the other one has to do with the absence of the Hall electric current (geometrical magnetoresistance) [1]. In the case when the relaxation time is independent of electron energy, the physical and geometrical contributions to the magnetoresistance cancel each other and the total magnetoresistance is zero [2].

In standard theory, magnetoresistance in isotropic semiconductors has only significant values in the case when the relaxation time depends on the energy, because the Lorentz force acts in a way on carriers with different velocities.

In all the theoretical papers, as far as galvanomagnetic effects in bulk semiconductors are concerned, the electric field E_x is usually considered independent of the magnetic field and coordinates as well as the size of the sample. However, in reality it is usual to establish some specific boundary conditions on the surfaces of the sample and as a consequence, in general, the electrostatic field is function of the coordinates and magnetic field in this bounded semiconductor (the corresponding result is written below).

Most of the boundary conditions used in the investigation of the galvanomagnetic effects in semiconductors have been focused only by considering a finite system along the Hall field [2]. Very recently Akhiezer, Gurevich and Zakirov [3], developed a theory of Hall effect and magnetoresistance in weak electric and magnetic fields for semiconductor samples of finite dimensions in all directions. The existence of vortex electric currents as a consequence of the finiteness of the sample, and magnetoresistance were obtained as a linear function of the magnetic field. The current distribution in this bounded system was computed and compared for different sample geometries. However, in the limit when the dimensions of the semiconductor are very large, the effects of the magnetic field disappears.

Sokolov et.al. [4], have been discussed that in a sample with arbitrary geometry in weak electric and magnetic fields the expression of the magnetoresistance, proportional to $(\omega_H \tau)^2$, changes substantially. However, when the dimensions of the specimen are very large, the usual result is recovered.

In this letter, we will quantitatively extend the analysis of magnetoresistance in bounded semiconductors in all directions. The analysis will show that it should be possible to observe a new and rather interesting electronic transport due to the dependence of the electric field on the magnetic field. In particular, specific definition of the boundary conditions for the potential at the surfaces, leads a change of the magnetoresistance in the limit of infinite system (bulk semiconductors) and it is not vanish when the relaxation time is indepen-

dent of energy. This remarkable result comes from the dependence of the x component of the electric field on the magnetic field by a term proportional to $(\omega_H\tau)^2$ which is finite when the dimensions of the sample are very large. This unusual behavior alter significantly the usual theory of galvanomagnetic effects developed for boundless media and conducting channels.

We shall assume that a semiconductor has the shape of a parallelepiped bounded by the $x = \pm a$, $y = \pm c$ and $z = \pm b$ planes and the $x = \pm a$ planes have the current contacts, while the magnetic field is directed along the y -axis. In this problem the geometry clearly is two-dimensional (all the quantities only depend of x and z). The electrostatic potential distribution in the sample can be found as a function of the coordinates and magnetic field by considering the current continuity equation. Under steady-state conditions, the electric current density $\mathbf{j}$ is described by the following expression [5]:

$$\mathbf{j} = e^2 I_{10} \mathbf{E} + (e^2 I_{20} \mathbf{E}) \times \mathbf{h} \quad (1)$$

and the continuity equation is:

$$\nabla \cdot \mathbf{j} = 0. \quad (2)$$

Assuming that the relaxation time is independent of electron energy (in this case magnetoresistance becomes zero in the conventional theory) and that the electron gas is nondegenerate (Maxwell statistics), the electron density with a quadratic and isotropic energy-momentum relation $\varepsilon = p^2/2m$ is

$$n = \frac{1}{2} \left(\frac{2m}{\pi \hbar^2} \right)^{3/2} T^{3/2} \exp(\mu/T_e)$$

the electric field is given by $\mathbf{E} = -\nabla\varphi$, φ is the electrostatical potential, μ the chemical potential, T the temperature, $\hbar = \mathbf{B}/B$ and

$$I_{10} = \frac{n\tau}{m} [1 - (\omega_H\tau)^2], \quad I_{20} = \frac{n\tau}{m} \omega_H\tau. \quad (3)$$

The expression for the average value of the current density over the cross section of the semiconductor significant for the magnetoresistance is given by

$$\bar{j}_x = \frac{1}{2b} \int_{-b}^{+b} j_x(x, z) dz. \quad (4)$$

The expression for $j_x(x, z)$ can be obtained from Eq. (1) and (2) with appro-

appropriate boundary conditions for the current density at the contacts i.e.

$$\varphi|_{x=\pm a} = \pm \frac{\Delta\varphi}{2} \quad (5)$$

where $\Delta\varphi$ is the difference potential applied to the sample. In addition, it is natural to choose $j_z = 0$ at $z = \pm b$, no contacts along the Hall field.

Substituting Eq. (3) into Eq. (1) and (2) and assuming that the electric field is weak, so that nonlinear effects (Joule heating) are negligible in Eq. (2), we can write the equations for the potential $\varphi(x, z)$ in the sample up to terms proportional to B^2 as

$$\nabla^2 \varphi(x, z) = 0, \quad (6)$$

The potential distribution satisfies the following equations at the surface of the sample where $j_z|_{z=\pm b} = 0$:

$$\left. \frac{\partial \varphi}{\partial z} + \omega_H \tau_0 \frac{\partial \varphi}{\partial x} \right|_{z=\pm b} = 0. \quad (7)$$

Assuming $\Delta\varphi$ to be small, we naturally seek solution of the Eq. (6) in the form

$$\varphi = \varphi_0 \Delta\varphi + \varphi_1 \Delta\varphi (\omega_H \tau_0) + \varphi_2 (\omega_H \tau_0)^2 \quad (8)$$

The quadratic correction to the potential with respect to the magnetic field is the important contribution to the magnetoresistance. Substituting Eq. (8) into Eq. (5) and (6), for the linear approximation in $\Delta\varphi$ and zeroth approximation with respect to the magnetic field, we find the well known expressions for the potential, the electric field and the current density:

$$\varphi_0 = -\frac{1}{2a}x, \quad E_x^0 = \frac{\Delta\varphi}{2a}, \quad E_z^0 = 0; \quad j_x^0 = \sigma_0 \frac{\Delta\varphi}{2a}; \quad j_z^0 = 0, \quad (9)$$

where

$$\sigma_0 = \frac{ne^2\tau}{m}$$

is the electric conductivity of electrons in the absence of magnetic field.

For linear approximation in the magnetic field, $\Delta\varphi(\omega_H\tau)$, we also employ Eq. (6) and (8), we can easily obtain the following differential equation for φ_1

$$\nabla^2\varphi_1(x, z) = 0 \quad (10)$$

indeed, with the conditions (5) and (7) satisfied, we may write

$$\varphi_1|_{x=\pm a} = 0, \quad \left. \frac{\partial\varphi_1}{\partial z} \right|_{z=\pm b} = \frac{1}{2a}. \quad (11)$$

Combining Eq. (10) and (11), we find the correction for the potential distribution to first order approximation with respect to the magnetic field

$$\varphi_1 = \frac{1}{a^2} \sum_{n=0}^{\infty} \frac{(-1)^n}{\alpha_n^2} \frac{\sinh \alpha_n z}{\cosh \alpha_n b} \cos \alpha_n x. \quad (12)$$

Here

$$\alpha_n = \frac{\pi}{2a}(2n+1).$$

It follows from Eq. (1) and Eq. (12), the x -component of the current density to first order in the magnetic field is given by

$$j_x = -\sigma_0 \frac{\partial\varphi_0}{\partial x} \Delta\varphi - \sigma_0 \frac{\partial\varphi_1}{\partial x} \Delta\varphi(\omega_H\tau) = j_0 \Delta\varphi + j_1 \Delta\varphi(\omega_H\tau) \quad (13)$$

with

$$j_1 = \frac{\sigma_0}{a^2} \sum_{n=0}^{\infty} \frac{(-1)^n}{\alpha_n} \frac{\sinh \alpha_n z}{\cosh \alpha_n b} \sinh \alpha_n x \quad (14)$$

It can be seen from expression (4) that the average value of the contribution to the current density in the linear approximation vanishes i.e. there is not magnetoresistance proportional to B , in other words

$$\bar{j}_1(x) = \frac{1}{2b} \int_{-b}^{+b} j_1(x, z) dz = 0.$$

Moving on to the calculations of the coefficient of $\varphi_2(x, z)$, we begin with the explicit equation which determines this quantity: it satisfies a similar expression

that Eq. (10) and from the boundary conditions Eq. (5) and (7) we can write

$$\varphi_2|_{x=\pm a} = 0, \quad \left. \frac{\varphi_2}{\partial z} + \frac{\partial \varphi_1}{\partial x} \right|_{z=\pm b} = 0. \quad (15)$$

In order to evaluate φ_2 it is convenient to use the following Fourier expansion of $\sin \alpha_n x$ in expression (12) only valid inside the semiconductor

$$\sin \alpha_n x = (-1)^n \frac{2}{a} \sum_{m=0}^{\infty} (-1)^m \frac{\beta_m}{\beta_m^2 - \alpha_n^2} \sin \beta_m x, \quad \beta_m = \frac{m\pi}{a}.$$

After some tedious but straightforward algebra, the general expression for φ_2 is given by

$$\varphi_2(x, z) = \frac{2}{a^3} \sum_{n,m=0}^{\infty} (-1)^{m+1} \frac{\tanh \alpha_n b}{\alpha_n} \frac{\cosh \beta_m z}{\sinh \beta_m z} \frac{\sinh \beta_m x}{\beta_m^2 - \alpha_n^2}.$$

Now, it is possible to write the x -component to the current density in second order to the magnetic field

$$j_x = j_0 \Delta \varphi + j_1 \Delta \varphi (\omega_H \tau) + j_2 \Delta \varphi (\omega_H \tau)^2,$$

where

$$j_2 = \sigma_0 \left(\frac{\partial \varphi_0}{\partial x} + \frac{\partial \varphi_1}{\partial z} - \frac{\partial \varphi_2}{\partial x} \right). \quad (16)$$

It is important to note that in the latter expression in second member, the first and second terms represent the physical and geometrical contribution to the magnetoresistance respectively. However, the last term is a new expression connected with the dependence of the x -component of the electric field in second order on the magnetic field.

Then the average value of the contribution to the current density in the second order approximation is given by

$$\bar{j}_2 = \sigma_0 \left(-\frac{1}{2a} - \frac{1}{a^3 b} \sum_{n=0}^{\infty} \frac{\tanh \alpha_n b}{\alpha_n^3} \right) \quad (17)$$

If $a \gg b$ (bulk semiconductor), from Eq. (17), we can obtain the following expression

$$\bar{j}_2 = -\frac{\sigma_0}{a}$$

It is straightforward to show, that in this limit the sum of the physical and geometrical contribution in Eq. (16) is vanish, this corresponds to the result of the conventional theory of magnetoresistance. Nevertheless, the extr term in Eq. (16) corresponds to the contribution to the x component of the electric field in second order to the magnatic field and this is not vanish in this limit.

The reason why the magnetoresistance is not zero in this theory comes from the behaviour of the potential near the contacts, in the regions $a - |x| \ll b$. In this region $\varphi_1(x, z = b)$ changes from 0 at the contacts, see Eq. (11), to $b/2a$, see Eq. (12), in the limit $a \gg b$. This means that in the boundary conditions for φ_2 , Eq. (15), $\partial\varphi_1/\partial x \geq 1/a$.

For the case when the relaxation time depends on the energy we obtain besides the usual results of magnetoresistance theory a different expression of the new term. It is worth to mention that in this situation the Ettingshausen effect (see Ref. [2]) plays an important role in magnetoresistance.

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